

- C1
Sub E
Concl'd
- (3) using one or more wires to electrically couple the transistor input terminal to an input matching element, an input signal lead, or both; and
- (4) setting the impedance of the one or more wires based at least in part on the measured transistor performance characteristic from step (2).

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- C2
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5. (Amended) A method of manufacturing a power transistor circuit, comprising carrying out the following steps in the enumerated order:

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- (1) securing a die to a substrate, the die comprising a transistor having an output terminal;
- (2) measuring a performance characteristic of the transistor;
- (3) using one or more wires to electrically couple the transistor output terminal to an output matching element, an output signal lead, or both; and
- (4) setting the impedance of the one or more wires based at least in part on the measured transistor performance characteristic from step (2).

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- C3
9. (Amended) A power transistor circuit, comprising:
- a substrate;
- a die secured to the substrate, the die comprising a transistor having an input terminal;
- 20 one or both of an input lead and an input matching element secured to the substrate;
- and

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one or more wires electrically coupling the transistor input terminal to the one or both of the input matching element and input signal lead, wherein the impedance of the one or more wires is selected based at least in part on a performance characteristic of the transistor measured after the die is secured to the substrate.

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13. (Amended) A power transistor circuit, comprising:

a substrate;

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a die secured to the substrate, the die comprising a transistor having an output terminal;

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one or both of an output lead and an output matching element secured to the substrate; and

one or more wires electrically coupling the transistor output terminal to the one or both of the output matching element and output signal lead, wherein the impedance of the one or more wires is selected based at least in part on a performance characteristic of the transistor measured after the die is secured to the substrate.

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